



09/989,770

JK

PATENTS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Jack Oon Chu, et al.

Docket: 17177A

Patent No: 6,858,502

Dated: July 15, 2005

Issued: February 22, 2005

For: HIGH SPEED COMPOSITE P-CHANNEL SI/  
SIGE HETEROSTRUCTUR FOR FIELD  
EFFECT DEVICE

Commissioner of Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Certificate  
JUL 22 2005  
of Correction

REQUEST FOR CERTIFICATE OF CORRECTION

Sir:

It appearing that errors have been introduced in the course of printing the  
Patent issued in the above application,  
it is respectfully requested that the Commissioner issue a Certificate of Correction in the  
following respects:

Column 1, Line 23:

“(HFMTs)” should read -- (HEMTs) --

Column 2, Line 27:

“ $Si_{1-x}Ge_w$ ” should read --  $Si_{1-w}Ge_w$  --

**Column 12, Line 19:**

**“Si<sub>1-w</sub>Ge<sub>x</sub>” should read -- Si<sub>1-w</sub>Ge<sub>w</sub> --**

**Column 13, Line 29:**

**“below the a channel” should read -- below a channel --**

**Column 14, Line 46:**

**“layer fanned” should read -- layer formed above --**

**Column 14, Line 49:**

**“method of fanning” should read -- method of forming --**

**Column 15, Line 24:**

**“dram electrode” should read -- drain electrode --**

**It is further noted that additional errors typographical in nature are incorporated into the printed specification, but are believed to be satisfactorily clear in the context and accordingly it is simply requested that this paper be made of record in the file for such clarification as may be appropriate. They are as follows:**

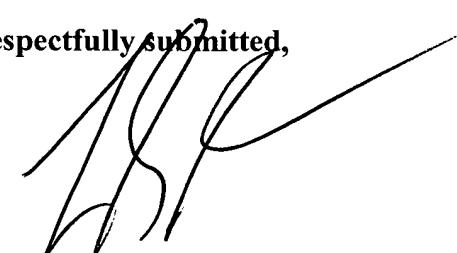
**Column 3, Line 61:**

“Field effect” should read --field-effect --

**Column 6, Line 42:**

“ $\text{Si}_{0.65}\text{Ge}_{0.35}$ ” should read --  $\text{Si}_{0.65}\text{Ge}_{0.35}$  --

Respectfully submitted,



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UNITED STATES PATENT AND TRADEMARK OFFICE  
CERTIFICATE OF CORRECTION

PATENT NO : **6,858,502**

APPLICATION NO : **09/989,770**

ISSUE DATE : **February 22, 2005**

INVENTOR(S) : **Jack Oon Chu, et al.**

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

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MAILING ADDRESS OF SENDER:

PATENT NO. 6,858,502

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